

Fast Response GaAs Photodetector Base on Constructing Electron Transmission Channel

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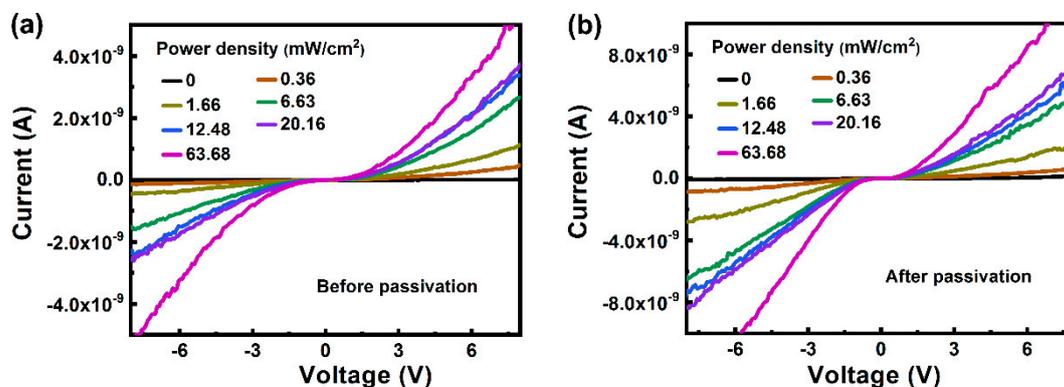


Figure S1. The I-V characteristic curves of the GaAs 2DNLS photodetector under different power densities (a) before and (b) after passivation.